Silicon NPN transistor epitaxial type
DP006

[Applications]
General purpose

[Feature]
Low collector saturation voltage VCE(sat)= 0.33V(Max.) at IC= 100mA, IB= 10mA

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	80	V
Collector-emitter voltage	VCEO	80	V
Emitter-base voltage	VEBO	4	V
Collector current	IC	0.5	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	80	-	-	V	IC= 100uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	80	-	-	V	IC= 1mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	4	-	-	V	IE= 100uA, IC= 0A
Collector-cut off current	ICEO	-	-	100	nA	VCE= 60V, IB= 0A
Collector-cut off current	ICBO	-	-	100	nA	VCB= 80V, IE= 0A
Emitter-cut off current	IEBO	-	-	100	nA	VEB= 5V, IC= 0A
DC current gain 1	hFE 1	90	-	-	-	VCE= 1V, IC= 10mA
DC current gain 2	hFE 2	90	-	-	-	VCE= 1V, IC= 100mA
Collector-emitter saturation voltage	VCE(sat)	-	-	0.33	V	IC= 100mA, IB= 10mA